

isc Silicon NPN Power Transistor

DESCRIPTION

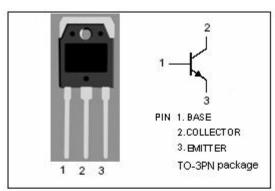
- · High Breakdown Voltage-
 - : V_{(BR)CBO}= 500V(Min)
- · High Switching Speed
- Low Collector Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

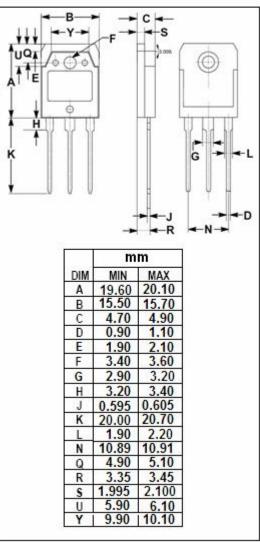
APPLICATIONS

• Designed for high speed power switching applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--|---------|---------------|
| Vсво | Collector-Base Voltage | 500 | V |
| V _{CEO} | Collector-Emitter Voltage | 400 | V |
| V _{EBO} | Emitter-Base Voltage | 7 | V |
| lc | Collector Current-Continuous | 7 | А |
| Ісм | Collector Current-Peak | 15 | А |
| Pc | Collector Power Dissipation @ T_c =25 $^{\circ}$ C | 70 | W |
| TJ | Junction Temperature | 150 | $^{\circ}$ |
| T _{stg} | Storage Temperature Range | -55~150 | ${\mathbb C}$ |







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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

| TC-20 © unicos outerwise specificu | | | | | | | | |
|------------------------------------|--------------------------------------|--|-----|------|-----|------------|--|--|
| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT | | |
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | I _C = 30mA; I _B = 0 | 400 | | | ٧ | | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 3A; I _B = 0.6A | | | 1.0 | ٧ | | |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | Ic= 3A; I _B = 0.6A | | | 1.5 | V | | |
| Ісво | Collector Cutoff Current | V _{CB} = 500V; I _E = 0 | | | 0.1 | mA | | |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 0.1 | mA | | |
| h _{FE-1} | DC Current Gain | I _C = 0.1A; V _{CE} = 5V | 15 | | | | | |
| h _{FE-2} | DC Current Gain | Ic= 3A; Vc== 5V | 8 | | | | | |
| f⊤ | Current-Gain—Bandwidth Product | Ic= 0.5A; VcE= 10V | | 11 | | MHz | | |
| Switching times | | | | | | | | |
| t _{on} | Turn-on Time | | | | 1.0 | μ \$ | | |
| t _{stg} | Storage Time | I _C = 3A, I _{B1} = -I _{B2} = 0.6A | | | 3.0 | μ \$ | | |
| tf | Fall Time | | | | 1.0 | μ s | | |

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